

BACK-END

MOS-FET

IGBT

DIODE

SCR

THERMAL RESISTANCE TESTER 過渡熱抵抗測定器

DDVF030ZZ

3200A

with repeat function
(リピート機能付)

- DDVF030ZZ has been designed to measure IGBT, MOS-FET, diode, and thyristor with 3200A (1ms) forcing ability at maximum. This tester has repeat test function of 9999 times, which is able to carry out screening test for device.
- DDVF030ZZはIGBT、MOS-FET、ダイオード、サイリスタの測定を可能とし、最大3200A（1ms）の印加能力を持っています。さらに9999回のリピートテスト機能を持ち、デバイスのスクリーニングを可能としています。

MODEL	DDVF030ZZ
MEASURABLE DEVICES	DIODE, IGBT, SCR, N MOS-FET
DETECT RANGE	
V _{F1} /V _{F2}	0mV~8191mV
ΔV _{F1}	0mV~1999mV
V _P	0mV~5000mV
	[Thermal resistance test, Repeat test]
V _F /V _{DS} /V _{CE} /V _T	0mV~5000mV [V _F]
V _{GS} /V _{GE}	0mV~8191mV [V _{th}]
I _F	0A~3200A
I _M	0A~10.00A
T _h	0°C~400.0°C
REPEAT	1~9999
BINNING	
OPEN/SHORT CHECK	V _{F1} >4V...OPEN V _{F1} <0.2V...SHORT
BIN INDICATION	PASS, LOW, HIGH, REJECT
DIMENSIONS & WEIGHT	
UNIT-A	550(W)×1400(D)×1700(H)…905kg
UNIT-B	550(W)×1400(D)×1700(H)…540kg



Forcing Power Range Diagram

[ΔV_F, ΔV_{CE}, ΔV_T, ΔV_{GK}, V_F, V_{CE}, V_T]